

ABSTRACT

WAFER PROCESSING METHOD

Disclosed herein is a wafer processing method including a first modified layer forming step of applying a laser beam having a transmission wavelength to a wafer from the back side thereof along each division line in the condition where the focal point of the laser beam is set inside the wafer near the front side thereof, thereby forming a first modified layer inside the wafer along each division line. The wafer processing method further includes a second modified layer forming step of applying the laser beam to the wafer from the back side thereof along each division line in the condition where the focal point of the laser beam is set adjacent to the first modified layer thereabove toward the back side of the wafer, thereby forming a second modified layer for growing a crack from the first modified layer toward the front side of the wafer.

(Figure 5C)